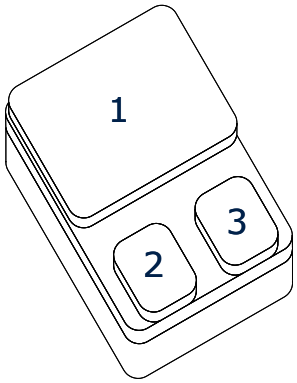
HiRel RadHard Power-MOS

- Low $R_{DS(on)}$
- Single Event Effect (SEE)
  LET 62, Range: 73µm (Xe)
  V_{GS} = -15V, V_{DS} = 650V
  V_{GS} = -20V, V_{DS} = 350V
- Total Ionisation Dose (TID)
  100 kRad (Level R)
- Hermetically sealed
- N-channel



Type	Marking	Pin Configuration 1	2	3	-	Package
BUY65CS28A-01	-	D	G	S	-	SMD2

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain Source Voltage	V_{DS}	650	V
Gate Source Voltage	V_{GS}	+/- 20	V
Drain Gate Voltage	V_{DG}	650	V
Continuous Drain Current T_C = 25 °C T_C = 100 °C	I_D	 28 18	A
Continuous Source Current	I_S	28	A
Drain Current Pulsed, t_p limited by T_{jmax}	I_{DM}	80	Apk
Total Power Dissipation [1)]	P_{tot}	250	W
Operating and Storage Temperature	T_{op}	-55 to + 150	°C
Avalanche Energy	E_{AS}	200	mJ

Thermal Characteristics

Thermal Resistance (Junction to Case)	$R_{th\ JC}$	0.58	K/W
Soldering Temperature	T_{sol}	250	°C

Notes.:

1) For $T_S \leq 25°C$. For $T_S > 25°C$ derating is required.

Electrical Characteristics, at T_A=25°C; unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown Voltage Drain to Source I_D = 0.25mA, V_{GS} = 0V	BV_{DSS}	650	-	-	V
Temperature Coefficiend of BV_{DSS}	$\Delta BV_{DSS}/\Delta T_J$	-	1.05	-	V/°C
Gate Threshold Voltage I_D = 1.0mA, $V_{DS} \geq V_{GS}$	$V_{GS(th)}$	2.0	-	4.0	V
Gate to Source Leakage Current V_{DS} = 0V, V_{GS} = +/- 20V	I_{GSS}	-	-	+/-100	nA
Drain Current V_{DS} = 520V, V_{GS} = 0V	I_{DSS}	-	-	25	µA
Drain Source On Resistance [1] V_{GS} = 10V, I_D = 18A	$r_{DS(ON)}$	-	116	150	mΩ
Source Drain Diode, Forward Voltage [1), 2)] V_{GS} = 0V, I_S = 28A	V_{SD}	-	-	1.2	V
AC Characteristics					
Turn-on Delay Time V_{DD} = 50% V_{DS}, I_D = 18A, R_G = 4.7Ω	$t_{d(ON)}$	-	22	28	ns
Rise Time V_{DD} = 50% V_{DS}, I_D = 18A, R_G = 4.7Ω	t_r	-	16	20	ns
Turn-off Delay Time V_{DD} = 50% V_{DS}, I_D = 18A, R_G = 4.7Ω	$t_{d(OFF)}$	-	53	80	ns
Fall Time V_{DD} = 50% V_{DS}, I_D = 18A, R_G = 4.7Ω	t_f	-	7	15	ns
Reverse Recovery Time $V_{DD} \leq$ 50V, I_D = 28A	t_{rr}	-	990	1080	ns
Common Source Input Capacitance V_{DS} = 100V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	4.1	4.8	5.5	nF
Common Source Output Capacitance V_{DS} = 100V, V_{GS} = 0V, f = 1.0MHz	C_{oss}	120	146	170	pF
Common Source Reverse Transfer Capacitance V_{DS} = 100V, V_{GS} = 0V, f = 1.0MHz	C_{rss}	5	11	17	pF
Gate Resistance	R_G	-	0.85	-	Ω
Total Gate Charge V_{DD} = 50% V_{DS}, V_{GS} = 10V, I_D = 28A	Q_G	-	67	85	nC

Notes.:
1) Pulsed Measurement: Pulse Width < 300µs, Duty Cycle <2.0%.
2) Measured within 2.0 mm of case.

Electrical Characteristics

at T_A=125°C; unless otherwise specified

Parameter	Symbol	Values		Unit
		min.	max.	
DC Characteristics				
Gate Threshold Voltage I_D = 1.0mA, $V_{DS} \geq V_{GS}$	$V_{GS(th)}$	1.5	-	V
Gate to Source Leakage Current V_{DS} = 0V, V_{GS} = +/- 20V	I_{GSS}	-	+/-200	nA
Drain Current V_{DS} = 520V, V_{GS} = 0V	I_{DSS}	-	250	µA
Drain Source On Resistance [1)] V_{GS} = 10V, I_D = 18A	$r_{DS(ON)}$	-	0.26	Ω

Notes.:

1) Pulsed Measurement: Pulse Width < 300µs, Duty Cycle <2.0%.

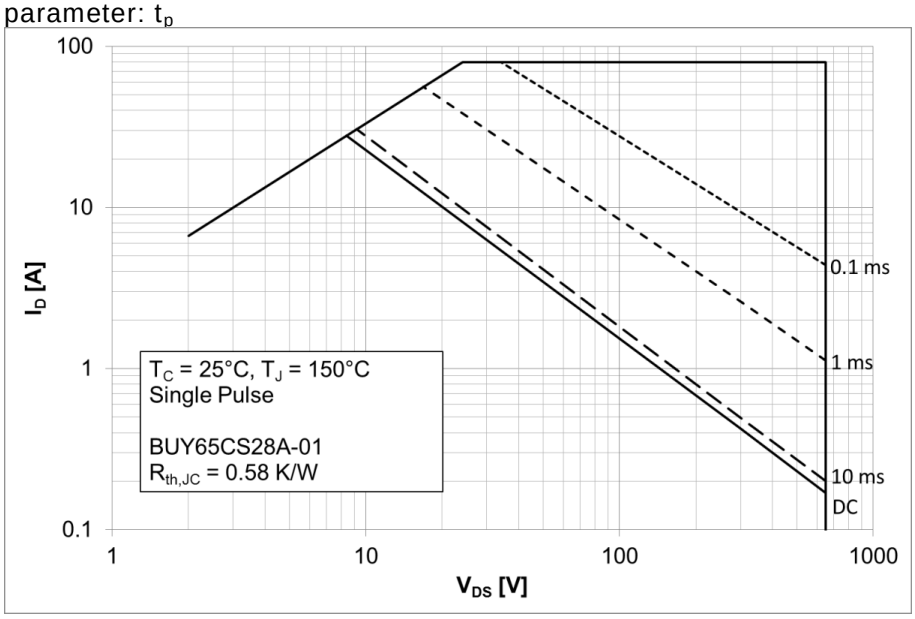
Electrical Characteristics

at T_A=-55°C; unless otherwise specified

Parameter	Symbol	Values		Unit
		min.	max.	
DC Characteristics				
Gate Threshold Voltage I_D = 1.0mA, $V_{DS} \geq V_{GS}$	$V_{GS(th)}$	-	5.0	V

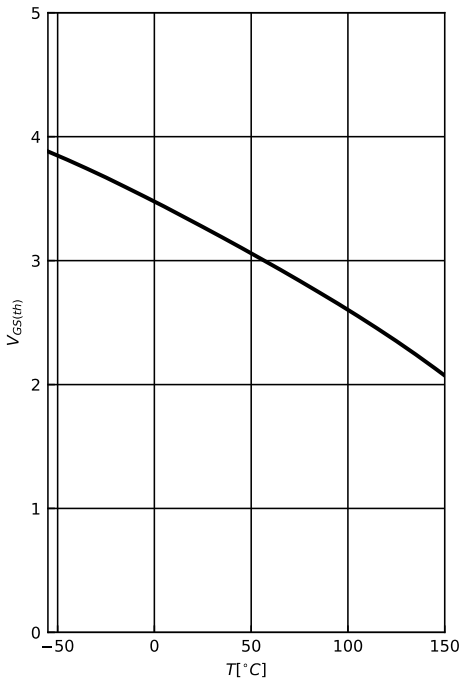
1 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25°C$
parameter: t_p



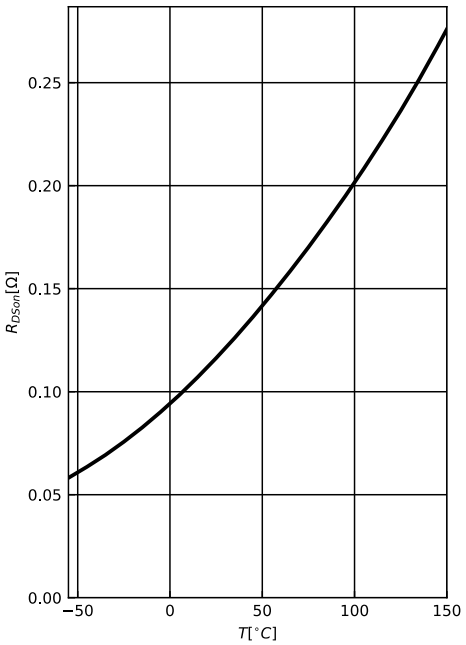
2 Typ. gate threshold voltage

$I_D=f(T_j)$
I_D = 1mA



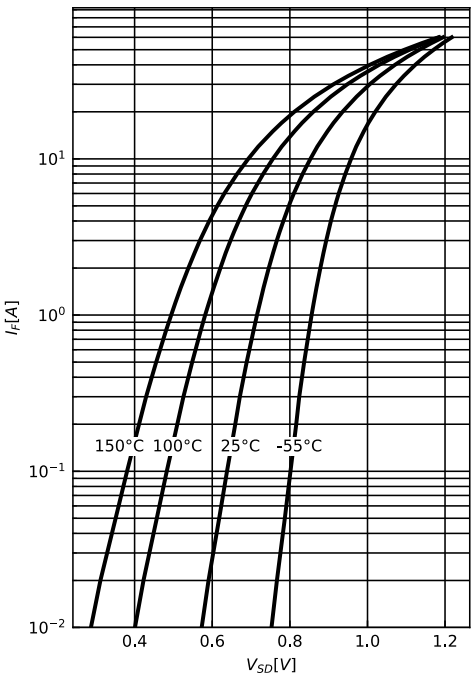
3 Typ. drain-source on-state resistance

$R_{DS(on)} = f(T_j)$
I_D=18A



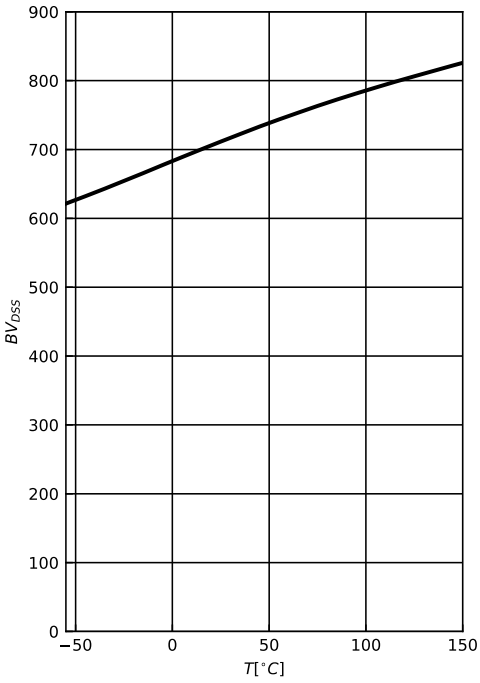
4 Typ. forward characteristics of reverse diode

$I_F = f(V_{SD})$
parameter: T_j



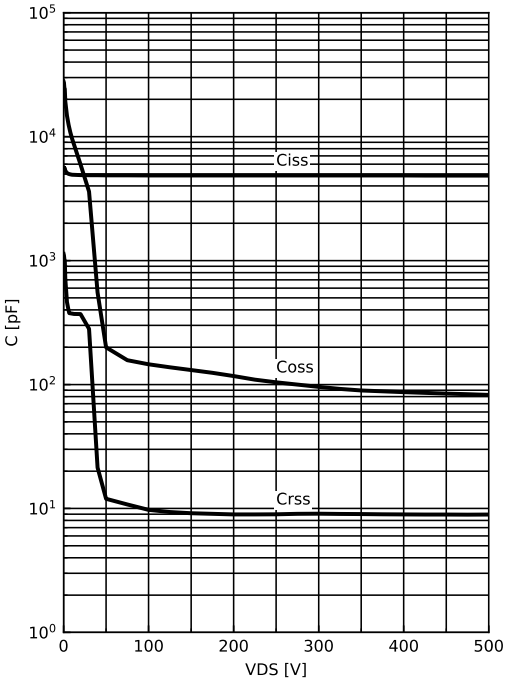
5 Typ. drain-source breakdown voltage

$BV_{DSS} = f(T_j)$
I_D = 250µA



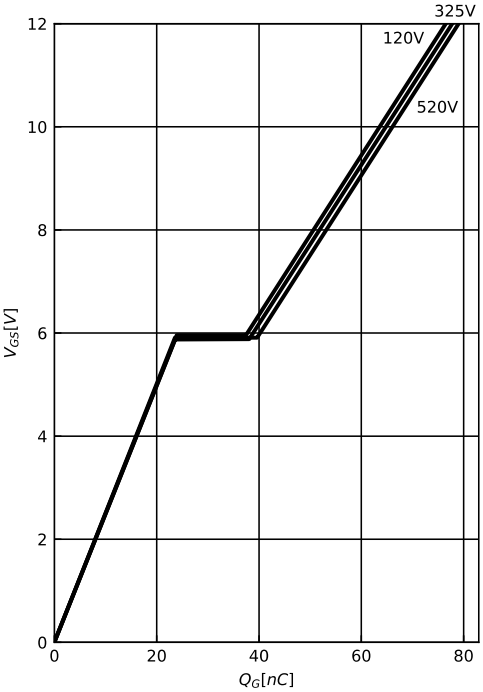
6 Typ. capacitances

$C = f(V_{DS})$; V_{GS} = 0 V; f = 1 MHz

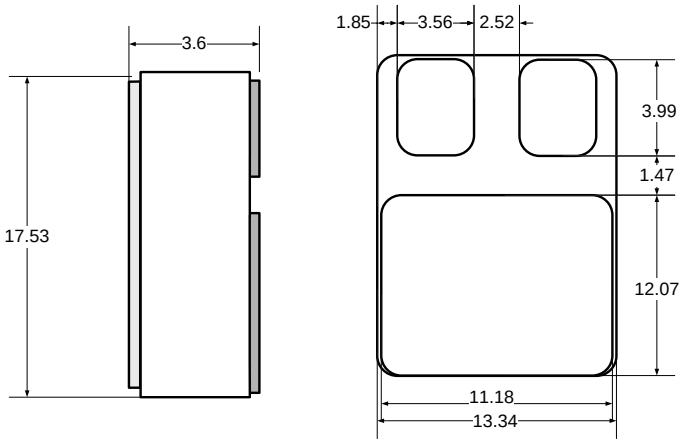


7 Typ. gate charge

$V_{GS} = f(Q_{gate})$; I_D = 28 A pulsed
parameter: V_{DD}



SMD2 Package



Dimensions are typical [mm]

Edition 2019-06
Published by
Infineon Technologies AG
85579 Neubiberg, Germany

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